

N-Ch MOSFET

#### **General Description**

The WSD60N10GDN56 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD60N10GDN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

#### **Product Summery**

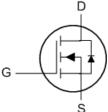
BV <sub>DSS</sub>		I <sub>D</sub>			
100V	8.5mΩ	60A			

#### Applications

- Power Management in TV Converter.
- DC-DC Converter
- LED TV Back Light

#### **DFN5X6** Pin Configuration





#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain-Source Voltage	100	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current	60	А	
I <sub>DP</sub>	Pulsed Drain Current	210	A	
EAS	Avalanche Energy, Single pulse	100	mJ	
P <sub>D</sub> @T <sub>C</sub> =25℃	Total Power Dissipation	125	W	
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	

#### Thermal Data

Symbol	Parameter	Тур.	Typ. Max.	
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>		60	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>		1.0	°C/W



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#### Electrical Characteristics (T\_J=25 $\ensuremath{\mathbb{C}}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	100			V
Р	Static Drain-Source On-Resistance	VGS=10V,ID=10A.		8.5	10.0	mΩ
R <sub>DS(ON)</sub>		VGS=4.5V,ID=10A.		9.5	12.0	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS}$ = $V_{DS}$ , $I_D$ =250uA	1.0		2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{\text{DS}}\text{=}80\text{V}$ , $V_{\text{GS}}\text{=}0\text{V}$ , $T_{\text{J}}\text{=}25^\circ\!\mathrm{C}$			1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm20V$ , $V_{DS}$ =0V			±100	nA
$Q_g$	Total Gate Charge (10V)	V <sub>DS</sub> =50V , V <sub>GS</sub> =10V , I <sub>D</sub> =25A		49.9		nC
Q <sub>gs</sub>	Gate-Source Charge			6.5		
$Q_gd$	Gate-Drain Charge			12.4		
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V , V <sub>GS</sub> =10V , R <sub>G</sub> =2.2Ω, I <sub>D</sub> =25A		20.6		ns
Tr	Rise Time			5		
T <sub>d(off)</sub>	Turn-Off Delay Time			51.8		
T <sub>f</sub>	Fall Time			9		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V , V <sub>GS</sub> =0V , f=1MHz		2604		pF
C <sub>oss</sub>	Output Capacitance			362		
Crss	Reverse Transfer Capacitance			6.5		
I <sub>S</sub>	Continuous Source Current	──V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			60	А
I <sub>SP</sub>	Pulsed Source Current				210	Α
V <sub>SD</sub>	Diode Forward Voltage	$V_{GS}$ =0V , $I_S$ =12A , $T_J$ =25 $^\circ\!\mathrm{C}$			1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I⊧=12A,dI/dt=100A/µs,Tյ=25℃		60.4		nS
Q <sub>rr</sub>	Reverse Recovery Charge			106.1		nC

#### Note

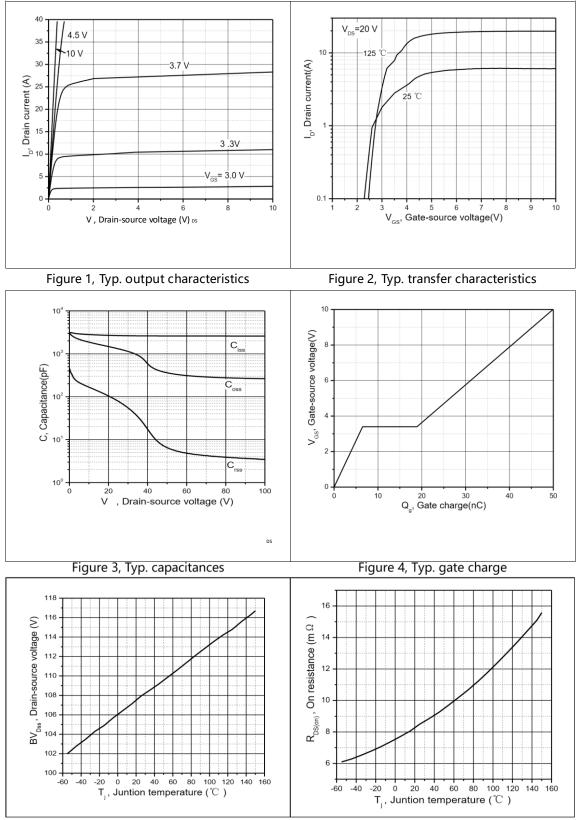
- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25$  °C.
- 5)  $V_{DD}$ =50 V,  $R_G$ =25  $\Omega$ , L=0.3 mH, starting  $T_j$ =25 °C.



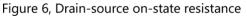
# WSD60N10GDN56

**N-Ch MOSFET** 

## **Typical Operating Characteristics**



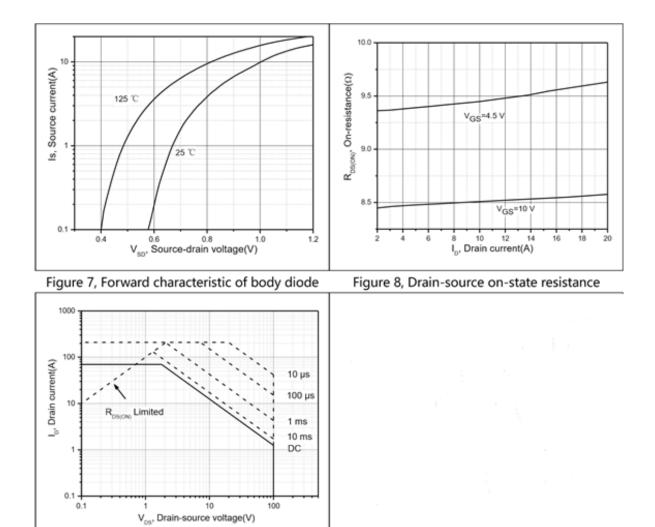






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## **Typical Operating Characteristics (Cont.)**





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